

42-DL211B

Version : A.008
Issue Date : 2008/06/19
File Name : SP-DL211B-A.008.doc
Total Pages : 6

Optical Fiber Transmitting IC



新竹市科學園區展業一路9號7樓之1
SILICON TOUCH TECHNOLOGY INC.
9-7F-1, Prosperity Road I, Science Based Industrial Park,
Hsin-Chu, Taiwan 300, R.O.C.
Tel : 886-3-5645656 Fax : 886-3-5645626

42-DL211B

OPTICAL FIBER TRANSMITTING IC

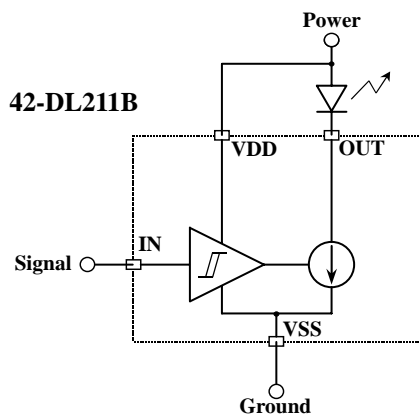
GENERAL DESCRIPTION

42-DL211B is a driver IC designed for the application of high-speed optical fiber transmission. It integrates the LED driver with constant current output to reduce the complexity and the cost of the transmission module. 42-DL211B can transmit with the speed up to 25Mb/s. 42-DL211B are fabricated by using CMOS technology with low power consumption purpose.

FEATURES

1. TTL interface compatible
2. High speed (up to 25Mb/s)
3. Uniform output waveform
4. Constant current output
5. Low power consumption
6. Wide range for Supply Voltage (2.7V-5.5V)

BLOCK DIAGRAM And APPLICATION CIRCUIT



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Supply Voltage	V_{DD}	-0.5 to +7	V
Input Voltage	V_{IN}	-0.5 to $V_{DD} + 0.5$	V
Operating Temperature	T_{opr}	-40 to +85	°C
Storage Temperature	T_{stg}	-55 to +100	°C
Electrostatic Damage	ESD	6.5	kV
Output Sinking Current	I_{OUT}	50	mA

RECOMMENDED OPERATING CONDITIONS

ITEM	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{DD}	2.7	-	5.5	V
High Level Input Voltage	V_{IH}	2.0	-	V_{DD}	V
Low Level Input Voltage	V_{IL}	0	-	0.8	V

ELECTRICAL CHARACTERISTICS ($V_{DD}=5.0V$, $T_A=25^{\circ}C$, if not mentioned)

ITEM	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
High Level Input Voltage	V_{IH}	$V_{DD}=3V$ or $5V$	2.0	-	V_{DD}	V
Low Level Input Voltage	V_{IL}	$V_{DD}=3V$ or $5V$	0	-	0.8	V
Input Leakage Current	I_{IN}	$V_{IN}=V_{DD}$ or V_{SS}	-	-	10	uA
Quiescent Supply Current	I_{DDQ}	$V_{IN}=V_{DD}$ or V_{SS}	-	4.0	-	mA
Output Sinking Current *Note1	I_{OUT_ON}	$V_{DD}=3V$ or $5V$, $V_{IN}=V_{DD}$, $V_{FLED}=2.0V$	2.4	3.0	3.6	mA
Output Leakage Current	I_{OUT_OFF}	$V_{DD}=3V$ or $5V$, $V_{OUT}=3V$, $V_{IN}=V_{SS}$	-	-	5	uA
Propagation Delay	T_{PLH} , T_{PHL}	$V_{DD}=3V$, $C_{LED}=15pF$, $V_{FLED}=2.0V$	-	-	40	ns
Rise Time, Fall Time of I_{OUT}	T_r , T_f	$V_{DD}=3V$, $C_{LED}=15pF$, $V_{FLED}=2.0V$	-	-	10	ns
Pulse Width Distortion	Δtw	$C_{LED}=15pF$, $V_{FLED}=2.0V$	- 10	0	10	ns
Jitter of Output Current	Δtj	$C_{LED}=15pF$, $V_{FLED}=2.0V$	-	1	25	ns
Data Rate	F_{DATA}	NRZ Code, $C_{LED}=15pF$, $V_{FLED}=2.0V$	-	-	25	Mb/s
Input Resistance *Note2	R_{IN}	multimeter	50	-	-	K Ω

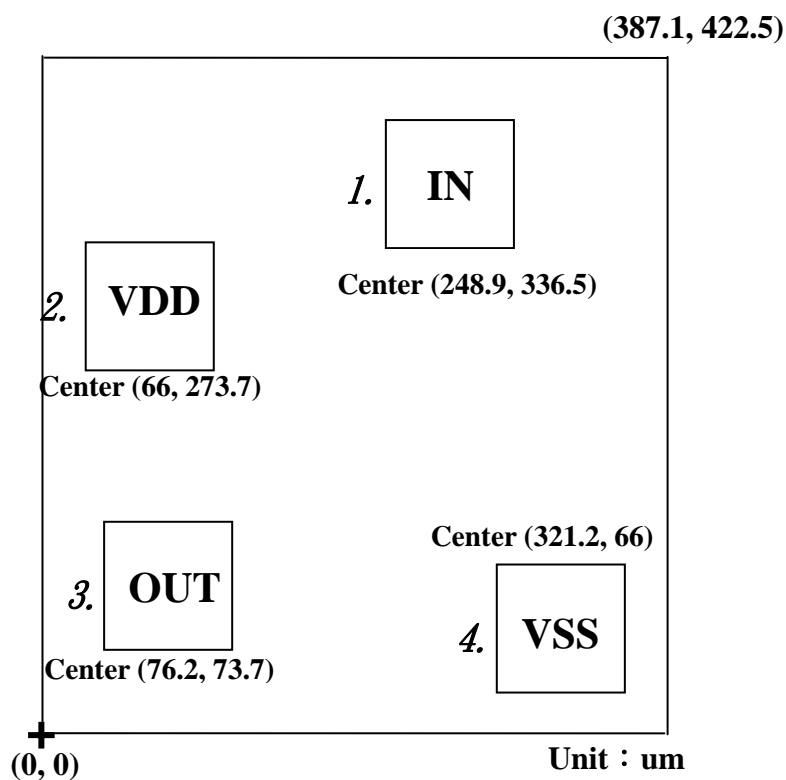
Note1 : $I_{OUT} = I_{OUT_OFF}$ when V_{in} =high, V_{DD} =floating.

Note2 : Typical value may be different due to different multimeters.

PAD DESCRIPTIONS

PAD NO.	PAD NAME	DESCRIPTIONS
1	IN	Input Pad(High Active)
2	VDD	Supply Voltage
3	OUT	Output Pad Sinking Current(Active Low)
4	VSS	Ground

DIE CONFIGURATION



Die Size: 387.1um * 422.5um

Die Thickness: 12mil(≒ 300um)

Pad Size: 90um * 90um

* **Note:** SiTI reserves the right to improve the device geometry and manufacturing processes without prior notice. Though these improvements may result in slight geometry changes, they will not affect die electrical characteristics and pad layouts.

REQUIREMENTS FOR WAFER DELIVERY

- Material : Silicon with P-Substrate
- Diameter : 6 inches(≒15cm)
- Thickness : 15 mils(≒381um)
- Malfunctioned die : Marked with red ink or equivalent marking

HANDLING RECOMMENDATION FOR STATIC ELECTRICITY PROTECTION

- (1) Avoid any circumstance that produce static electricity, e.g. rubbing against plastic, during moving, storing and processing 42-DL211B.
- (2) Process 42-DL211B in a clean room with proper temperature and humidity.
- (3) Ground all working machines and workers wear anti-electrostatic ring to ground during processing.
- (4) Avoid contact 42-DL211B with bare hands .If unavoided, wear anti-electrostatic ring and use anti-electrostatic tool to pick it up.

GUARANTED TEMPERATURE AND RETENTION CYCLE

- (1) The device/wafer 42-DL211B should be stored in the nitrogenous chest. The conditions suggested are as follows:
 - Temperature = $23\pm 3^{\circ}\text{C}$
 - Relative Humidity = $50\pm 10\%$
 - Minimum nitrogen inflow = 3 liters/minute
- (2) If the device/wafer, 42-DL211B is incidentally exposed to the air, use it for manufacturing as soon as possible.
- (3) Under the storage environment specified in item (1), six-month safe storage period is guaranteed.



The products listed herein are designed for ordinary electronic applications, such as electrical appliances, audio-visual equipment, communications devices and so on. Hence, it is advisable that the devices should not be used in medical instruments, surgical implants, aerospace machinery, nuclear power control systems, disaster/crime-prevention equipment and the like. Misusing those products may directly or indirectly endanger human life, or cause injury and property loss.

Silicon Touch Technology, Inc. will not take any responsibilities regarding the misuse of the products mentioned above. Anyone who purchases any products described herein with the above-mentioned intention or with such misused applications should accept full responsibility and indemnify. Silicon Touch Technology, Inc. and its distributors and all their officers and employees shall defend jointly and severally against any and all claims and litigation and all damages, cost and expenses associated with such intention and manipulation.